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Kind regards,

Team Nexperia

PDTA114Y series

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 47 k Ω

Rev. 5 — 18 November 2011

Product data sheet

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistor (RET) family in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package				Package	
	NXP	JEITA	JEDEC	complement	configuration	
PDTA114YE	SOT416	SC-75	-	PDTC114YE	ultra small	
PDTA114YM	SOT883	SC-101	-	PDTC114YM	leadless ultra small	
PDTA114YT	SOT23	-	TO-236AB	PDTC114YT	small	
PDTA114YU	SOT323	SC-70	-	PDTC114YU	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital applications in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
lo	output current		-	-	-100	mA
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		3.7	4.7	5.7	
-						



2. Pinning information

Table 3. Pinning

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
SOT23; S	SOT323; SOT416		
1	input (base)		
2	GND (emitter)	3	R1 3
3	output (collector)	1 2 006aaa144	1 R2 2 sym003
SOT883			
1	input (base)		
2	GND (emitter)	1 3	R1 3
3	output (collector)	2 Transparent top view	1 R2 sym003

3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
PDTA114YE	SC-75	plastic surface-mounted package; 3 leads	SOT416			
PDTA114YM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883			
PDTA114YT	-	plastic surface-mounted package; 3 leads	SOT23			
PDTA114YU	SC-70	plastic surface-mounted package; 3 leads	SOT323			

4. Marking

Table 5. Marking codes

[1] * = placeholder for manufacturing site code

5. Limiting values

Table 6. Limiting values

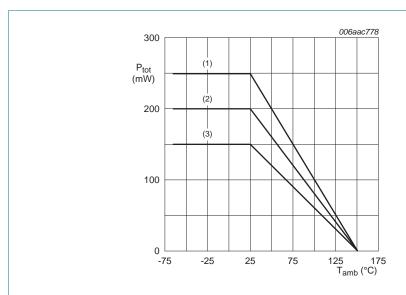
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
V_{I}	input voltage				
	positive		-	+6	V
	negative		-	-40	V
Io	output current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PDTA114YE (SOT416)		[1][2]	150	mW
	PDTA114YM (SOT883)		[2][3]	250	mW
	PDTA114YT (SOT23)		<u>[1]</u> -	250	mW
	PDTA114YU (SOT323)		<u>[1]</u> -	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



- SOT23; FR4 PCB, standard footprint
 SOT883; FR4 PCB with 70 μm copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PDTA114YE (SOT416)		[1][2]	-	830	K/W
	PDTA114YM (SOT883)		[2][3]	-	500	K/W
	PDTA114YT (SOT23)		<u>[1]</u> _	-	500	K/W
	PDTA114YU (SOT323)		<u>[1]</u> _	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.

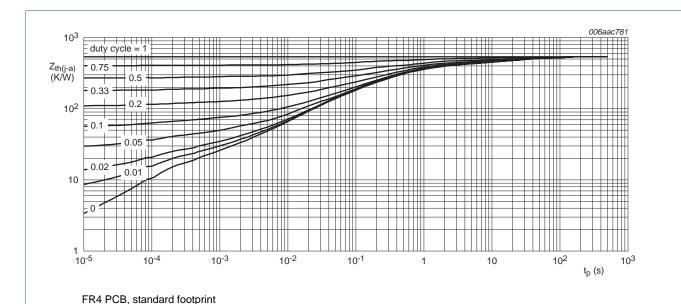


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114YE (SOT416); typical values

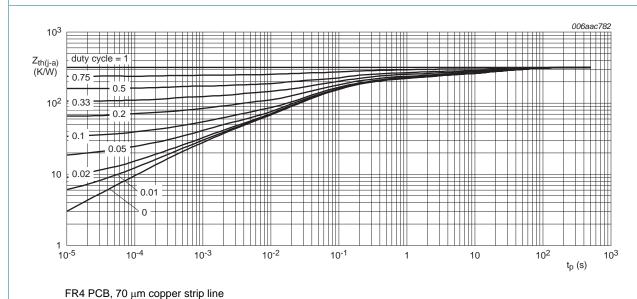


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114YM (SOT883); typical values

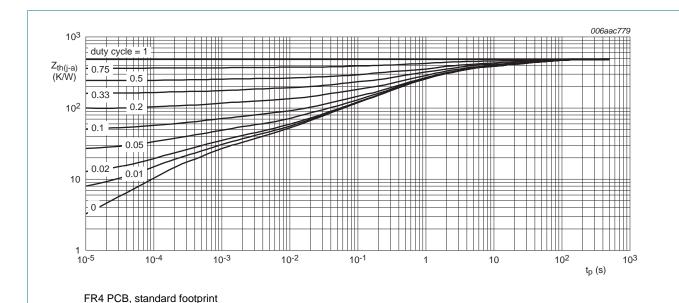


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114YT (SOT23); typical values

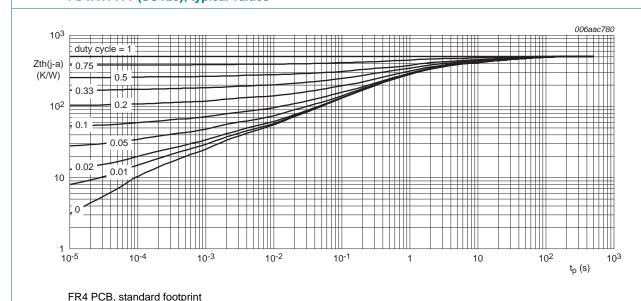


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114YU (SOT323); typical values

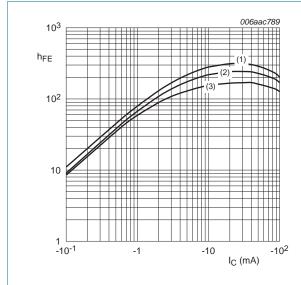
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	ceo collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	-	-	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-150	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$	-	-	-100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-0.7	-0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -1 \text{ mA}$	-1.4	-0.8	-	V
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		3.7	4.7	5.7	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}; $ [1] $f = 100 \text{ MHz}$	-	180	-	MHz

[1] Characteristics of built-in transistor



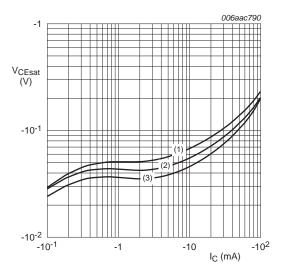


(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 6. DC current gain as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

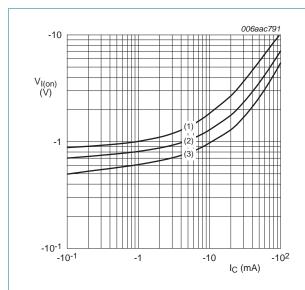
(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values

PDTA114Y_SER

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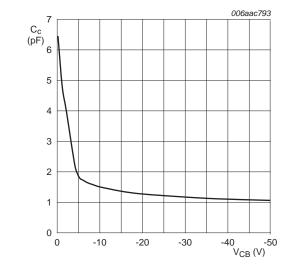
$$V_{CE} = -0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

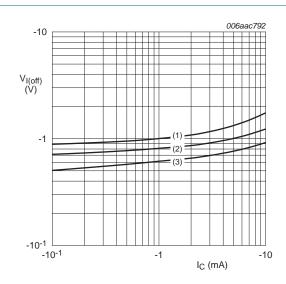
(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 8. On-state input voltage as a function of collector current; typical values



f = 1 MHz; T_{amb} = 25 °C

Fig 10. Collector capacitance as a function of collector-base voltage; typical values



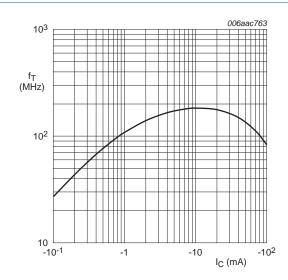
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 9. Off-state input voltage as a function of collector current; typical values



 $V_{CE} = -5 \text{ V}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

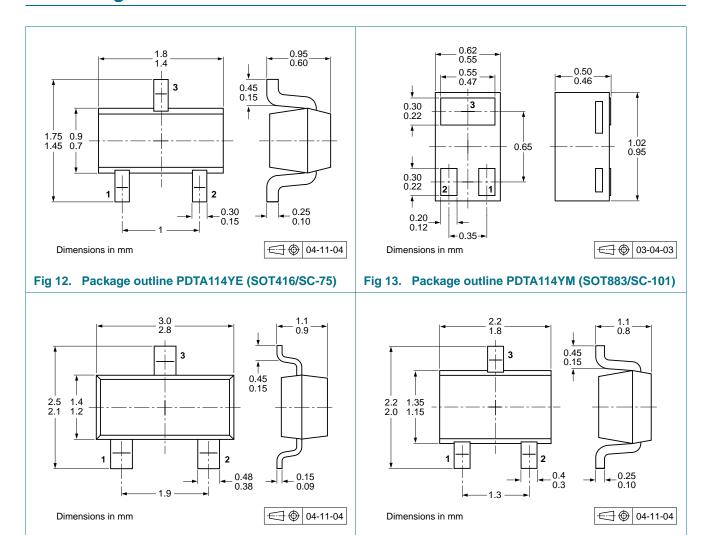


Fig 15. Package outline PDTA114YU (SOT323/SC-70)

Fig 14. Package outline PDTA114YT (SOT23)

10. Packing information

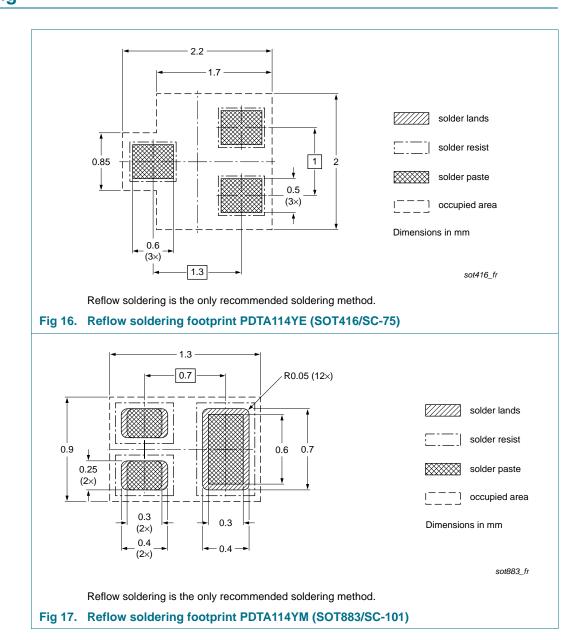
Table 9. Packing methods

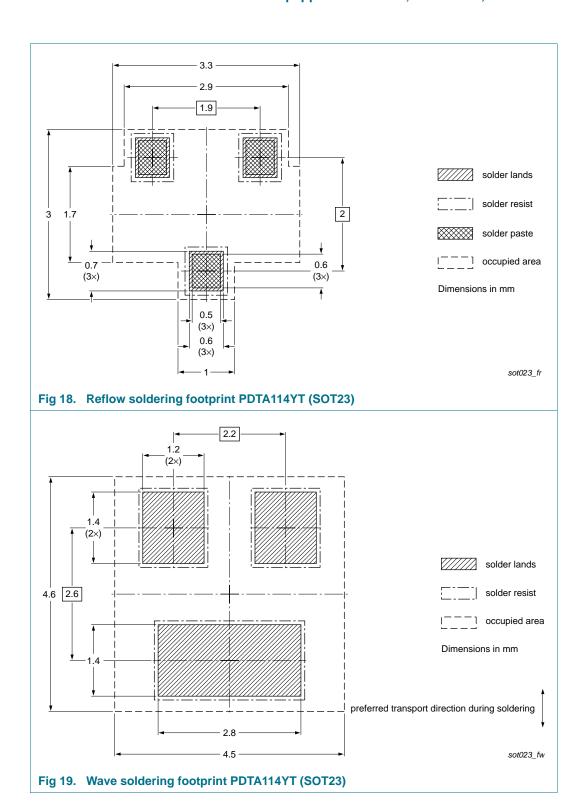
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

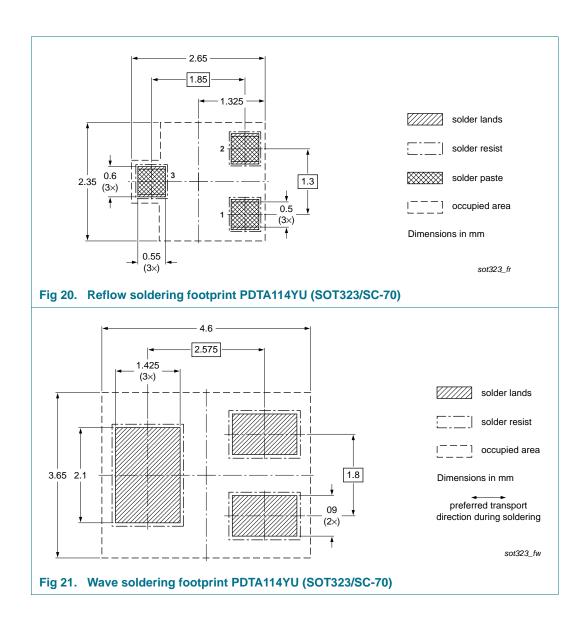
Type number	Package	Description	Packing	Packing quantity		
			3000	5000	10000	
PDTA114YE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135	
PDTA114YM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315	
PDTA114YT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235	
PDTA114YU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135	

^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering







12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PDTA114Y_SER v.5	20111118	Product data sheet	-	PDTA114Y_SERIES v.4		
Modifications:		f this document has been r NXP Semiconductors.	edesigned to comply wi	th the new identity		
	 Legal texts have 	ave been adapted to the ne	ew company name whe	re appropriate.		
	 Type numbers PDTA114YEF, PDTA114YK and PDTA114YS removed. 					
	 Section 1 "Pr 	oduct profile": updated				
	 Section 3 "Or 	dering information": added	I			
	 Section 4 "Magnetic Section 4" 	arking": updated				
	• <u>Figure 1</u> to <u>1</u>	1: added				
	Section 5 "Limiting values": updated					
	Section 6 "Thermal characteristics": updated					
	 <u>Table 8 "Characteristics"</u>: V_{i(on)} redefined to V_{I(on)} on-state input voltage, V_{i(off)} redefined to V_{I(off)} off-state input voltage, I_{CEO} updated, f_T added 					
	 Section 8 "Te 	st information": added				
	Section 9 "Package outline": superseded by minimized package outline drawings					
	 Section 10 "F 	Packing information": added	d			
	Section 11 "S	Section 11 "Soldering": added				
	 Section 13 "L 	egal information": updated	I			
PDTA114Y_SERIES v.4	20040802	Product data sheet	-	PDTA114Y_SERIES v.3		
PDTA114Y_SERIES v.3	20030909	Product specification	-	PDTA114Y_SERIES v.2		
PDTA114Y_SERIES v.2	20030411	Product specification	-	PDTA114YEF v.1		
PDTA114YEF v.1	20020515	Product specification	-	-		

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTA114Y_SER

PDTA114Y series

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 47 k Ω

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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14. Contact information

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PDTA114Y series

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 47 k Ω

15. Contents

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NSBC114YF3T5G NSBC123TF3T5G SMUN5235T1G SMUN5330DW1T1G SSVMUN5312DW1T2G RN1303(TE85L,F)

RN4605(TE85L,F) TTEPROTOTYPE79 DDTC114EUAQ-7-F EMH15T2R SMUN2214T3G SMUN5335DW1T1G NSBC114TF3T5G

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NSBA144EF3T5G NSVDTA114EET1G 2SC2223-T1B-A 2SC3912-TB-E SMUN5237DW1T1G SMUN5213DW1T1G

SMUN5114DW1T1G SMUN2111T1G NSVDTC144EM3T5G DTC124ECA-TP DTC123TM3T5G DTA114ECA-TP DTA113EM3T5G

DCX115EK-7-F DTC113EM3T5G NSVMUN5135DW1T1G NSVMUN2237T1G